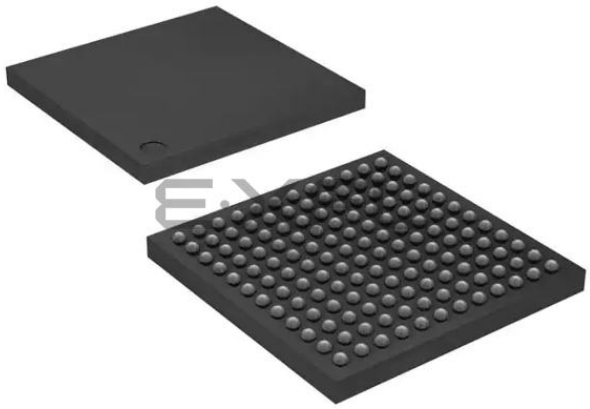

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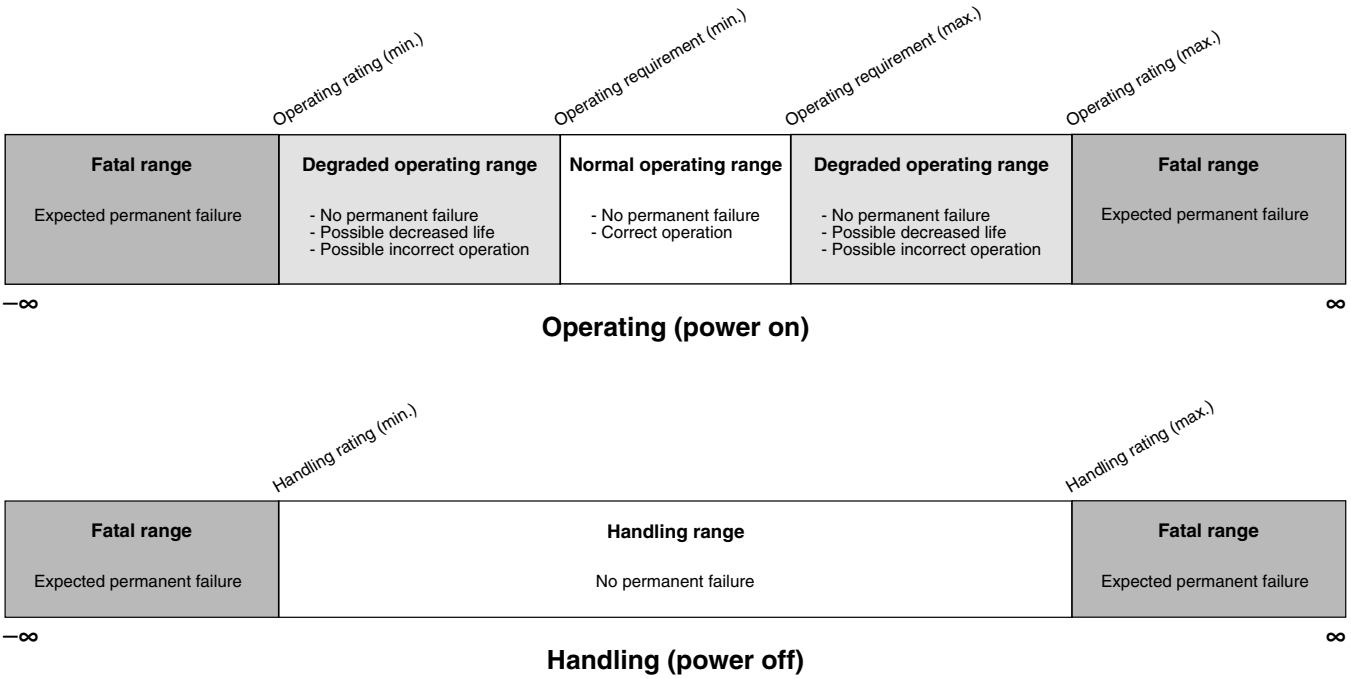
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SD, SPI, UART/USART
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	104
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 46x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LBGA
Supplier Device Package	144-MAPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dx256zvmd10

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

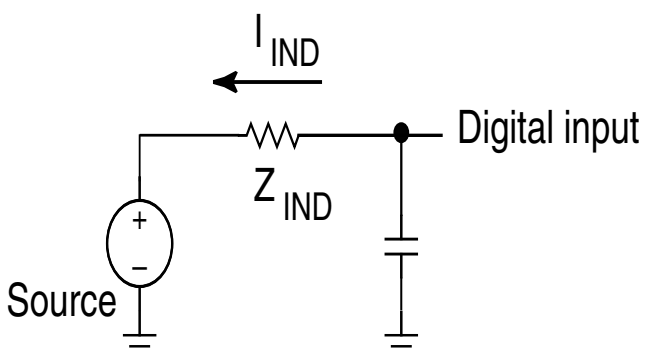
Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength					
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -9mA	V_{DD} – 0.5	—	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -3mA	V_{DD} – 0.5	—	—	V	
	Output high voltage — low drive strength					
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -2mA	V_{DD} – 0.5	—	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -0.6mA	V_{DD} – 0.5	—	—	V	
I_{OHT}	Output high current total for all ports	—	—	100	mA	
V_{OL}	Output low voltage — high drive strength					2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 9mA	—	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 3mA	—	—	0.5	V	
	Output low voltage — low drive strength					
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 2mA	—	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 0.6mA	—	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	—	100	mA	
I_{INA}	Input leakage current, analog pins and digital pins configured as analog inputs					3, 4
	• V_{SS} ≤ V_{IN} ≤ V_{DD}					
	— All pins except EXTAL32, XTAL32, EXTAL, XTAL	—	0.002	0.5	µA	
	— EXTAL (PTA18) and XTAL (PTA19)	—	0.004	1.5	µA	
	— EXTAL32, XTAL32	—	0.075	10	µA	
I_{IND}	Input leakage current, digital pins					4, 5
	• V_{SS} ≤ V_{IN} ≤ V_{IL}					
	— All digital pins	—	0.002	0.5	µA	
	• V_{IN} = V_{DD}					
	— All digital pins except PTD7	—	0.002	0.5	µA	
	— PTD7	—	0.004	1	µA	
I_{IND}	Input leakage current, digital pins					4, 5, 6
	• V_{IL} < V_{IN} < V_{DD}					
	— V_{DD} = 3.6 V	—	18	26	µA	
	— V_{DD} = 3.0 V	—	12	49	µA	
	— V_{DD} = 2.5 V	—	8	13	µA	
	— V_{DD} = 1.7 V	—	3	6	µA	

Table continues on the next page...

Table 4. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
I_{IND}	Input leakage current, digital pins • $V_{DD} < V_{IN} < 5.5$ V	— —	 1	 50	 μA	4, 5
Z_{IND}	Input impedance examples, digital pins • $V_{DD} = 3.6$ V • $V_{DD} = 3.0$ V • $V_{DD} = 2.5$ V • $V_{DD} = 1.7$ V	 — — — —	 — — — —	 48 55 57 85	 kΩ kΩ kΩ kΩ	4, 7
R_{PU}	Internal pullup resistors	20	35	50	kΩ	8
R_{PD}	Internal pulldown resistors	20	35	50	kΩ	9

1. Typical values characterized at 25°C and VDD = 3.6 V unless otherwise noted.
2. Open drain outputs must be pulled to V_{DD}.
3. Analog pins are defined as pins that do not have an associated general purpose I/O port function.
4. Digital pins have an associated GPIO port function and have 5V tolerant inputs, except EXTAL and XTAL.
5. Internal pull-up/pull-down resistors disabled.
6. Characterized, not tested in production.
7. Examples calculated using V_{IL} relation, V_{DD}, and max I_{IND}: $Z_{IND}=V_{IL}/I_{IND}$. This is the impedance needed to pull a high signal to a level below V_{IL} due to leakage when $V_{IL} < V_{IN} < V_{DD}$. These examples assume signal source low = 0 V.
8. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}
9. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{DD}



5.2.4 Power mode transition operating behaviors

All specifications except t_{POR}, and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 100 MHz
- Bus clock = 50 MHz
- FlexBus clock = 50 MHz
- Flash clock = 25 MHz
- MCG mode: FEI

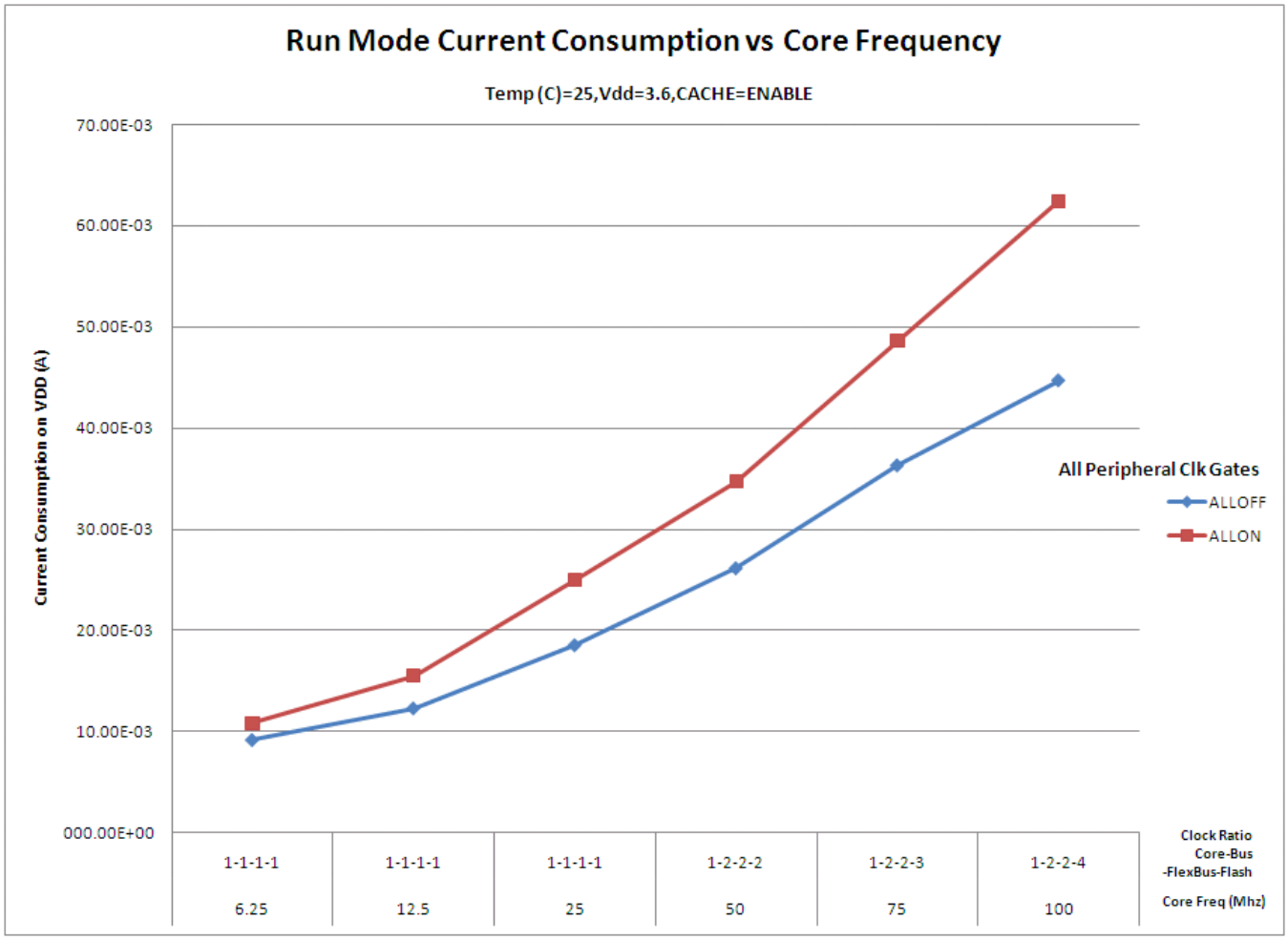


Figure 2. Run mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors as measured on 144LQFP and 144MAPBGA packages

Symbol	Description	Frequency band (MHz)	144LQFP	144MAPBGA	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	23	12	dBµV	1 , 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	27	24	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	28	27	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	14	11	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	K	K	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 12 MHz (crystal), f_{SYS} = 96 MHz, f_{BUS} = 48MHz
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	100	MHz	
f_{BUS}	Bus clock	—	50	MHz	
FB_CLK	FlexBus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	

5.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, CAN, CMT, and I^2C signals.

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

5.4.2 Thermal attributes

Board type	Symbol	Description	144 LQFP	144 MAPBGA	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	45	48	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	36	29	°C/W	1
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	36	38	°C/W	1
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	30	25	°C/W	1
—	$R_{\theta JB}$	Thermal resistance, junction to board	24	16	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	9	9	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	2	2	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.

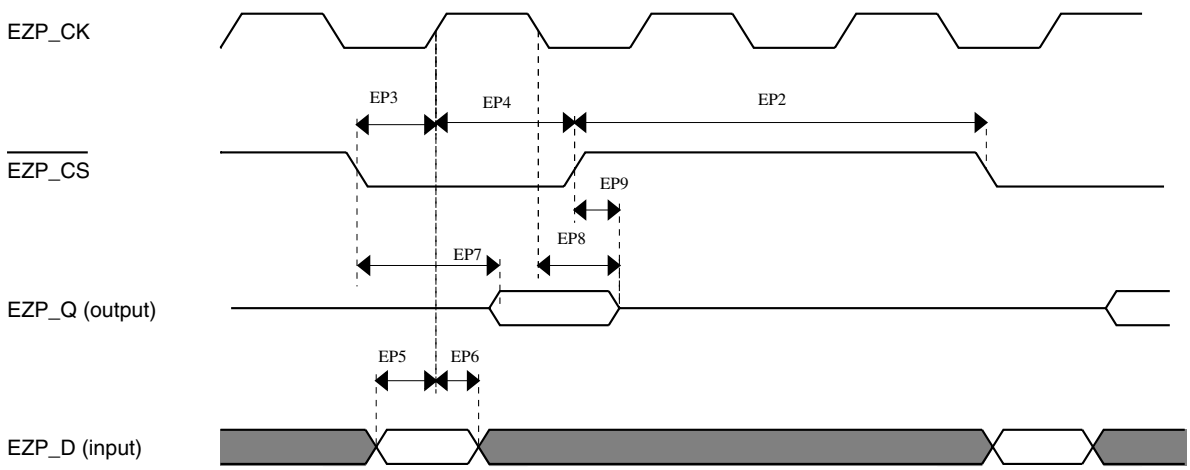


Figure 9. EzPort Timing Diagram

6.4.3 Flexbus Switching Specifications

All processor bus timings are synchronous; input setup/hold and output delay are given in respect to the rising edge of a reference clock, FB_CLK. The FB_CLK frequency may be the same as the internal system bus frequency or an integer divider of that frequency.

The following timing numbers indicate when data is latched or driven onto the external bus, relative to the Flexbus output clock (FB_CLK). All other timing relationships can be derived from these values.

Table 25. Flexbus limited voltage range switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	FB_CLK	MHz	
FB1	Clock period	20	—	ns	
FB2	Address, data, and control output valid	—	11.5	ns	1
FB3	Address, data, and control output hold	0.5	—	ns	1
FB4	Data and $\overline{\text{FB\_TA}}$ input setup	8.5	—	ns	2
FB5	Data and $\overline{\text{FB\_TA}}$ input hold	0.5	—	ns	2

1. Specification is valid for all FB_AD[31:0], $\overline{\text{FB\_BE/BWE}n}$, $\overline{\text{FB\_CS}n}$, $\overline{\text{FB\_OE}}$, FB_R/$\overline{\text{W}}$,$\overline{\text{FB\_TBST}}$, FB_TSIZ[1:0], FB_ALE, and $\overline{\text{FB\_TS}}$.

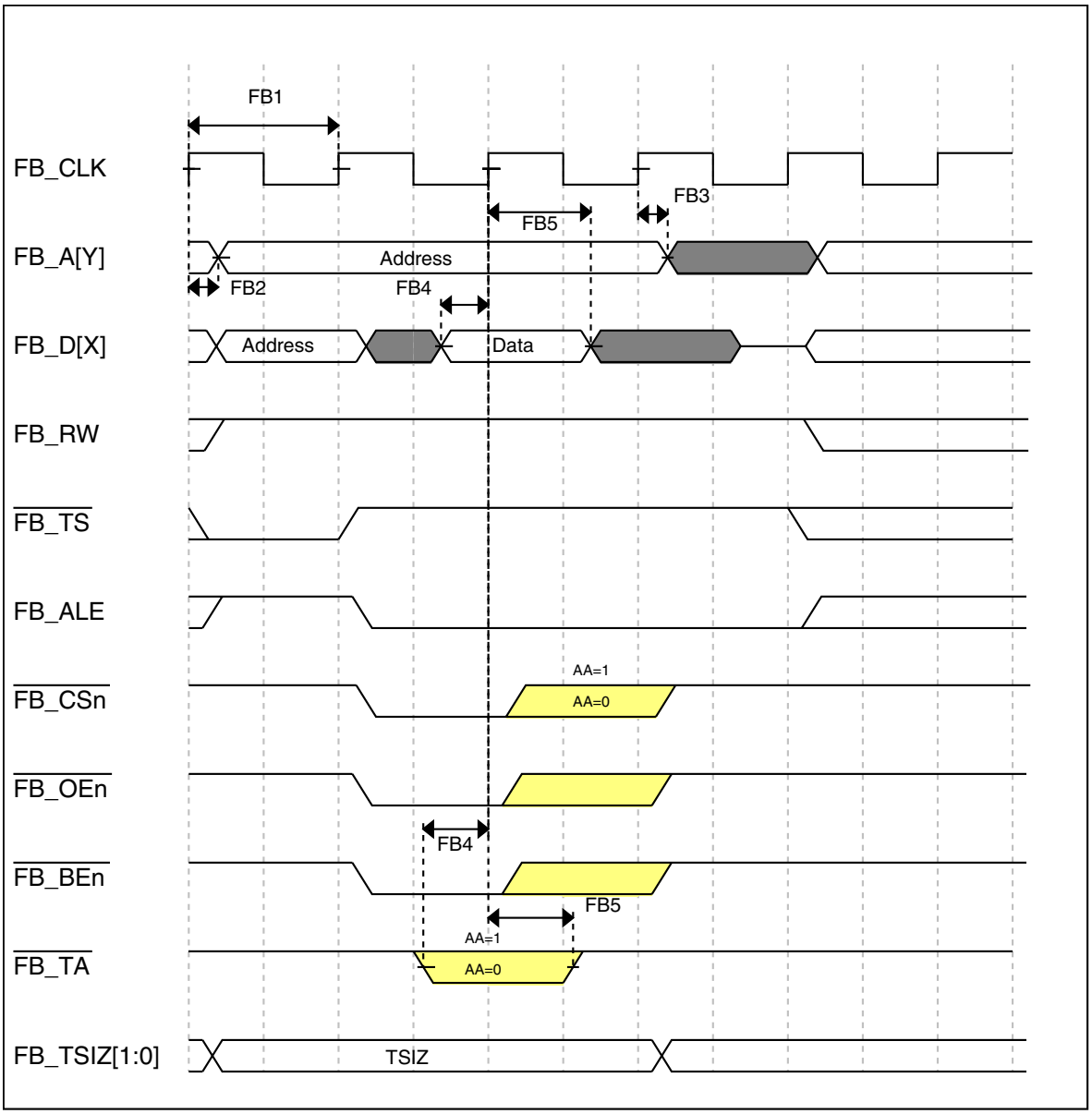


Figure 10. FlexBus read timing diagram

Table 29. 16-bit ADC with PGA operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
C_{rate}	ADC conversion rate	≤ 13 bit modes No ADC hardware averaging Continuous conversions enabled Peripheral clock = 50 MHz	18.484	—	450	Ksps	7
		16 bit modes No ADC hardware averaging Continuous conversions enabled Peripheral clock = 50 MHz	37.037	—	250	Ksps	8

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 6 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. ADC must be configured to use the internal voltage reference (VREF_OUT)
3. PGA reference is internally connected to the VREF_OUT pin. If the user wishes to drive VREF_OUT with a voltage other than the output of the VREF module, the VREF module must be disabled.
4. For single ended configurations the input impedance of the driven input is $R_{PGAD}/2$
5. The analog source resistance (R_{AS}), external to MCU, should be kept as minimum as possible. Increased R_{AS} causes drop in PGA gain without affecting other performances. This is not dependent on ADC clock frequency.
6. The minimum sampling time is dependent on input signal frequency and ADC mode of operation. A minimum of 1.25µs time should be allowed for F_{in}=4 kHz at 16-bit differential mode. Recommended ADC setting is: ADLSMP=1, ADLSTS=2 at 8 MHz ADC clock.
7. ADC clock = 18 MHz, ADLSMP = 1, ADLST = 00, ADHSC = 1
8. ADC clock = 12 MHz, ADLSMP = 1, ADLST = 01, ADHSC = 1

6.6.1.4 16-bit ADC with PGA characteristics

Table 30. 16-bit ADC with PGA characteristics

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
I_{DDA_PGA}	Supply current	Low power (ADC_PGA[PGALPb]=0)	—	420	644	µA	2
I_{DC_PGA}	Input DC current		$\frac{2}{R_{PGAD}}\left(\frac{(V_{REFPGA}\times 0.583)-V_{CM}}{(Gain+1)}\right)$			A	3
		Gain =1, V_{REFPGA}=1.2V, V_{CM}=0.5V	—	1.54	—	µA	
		Gain =64, V_{REFPGA}=1.2V, V_{CM}=0.1V	—	0.57	—	µA	

Table continues on the next page...

Table 30. 16-bit ADC with PGA characteristics (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
ENOB	Effective number of bits	• Gain=1, Average=4	11.6	13.4	—	bits	16-bit differential mode,f_{in}=100Hz
		• Gain=64, Average=4	7.2	9.6	—	bits	
		• Gain=1, Average=32	12.8	14.5	—	bits	
		• Gain=2, Average=32	11.0	14.3	—	bits	
		• Gain=4, Average=32	7.9	13.8	—	bits	
		• Gain=8, Average=32	7.3	13.1	—	bits	
		• Gain=16, Average=32	6.8	12.5	—	bits	
		• Gain=32, Average=32	6.8	11.5	—	bits	
		• Gain=64, Average=32	7.5	10.6	—	bits	
SINAD	Signal-to-noise plus distortion ratio	See ENOB	6.02 × ENOB + 1.76			dB	

1. Typical values assume V_{DDA} =3.0V, Temp=25°C, f_{ADCK}=6MHz unless otherwise stated.
2. This current is a PGA module adder, in addition to ADC conversion currents.
3. Between IN+ and IN-. The PGA draws a DC current from the input terminals. The magnitude of the DC current is a strong function of input common mode voltage (V_{CM}) and the PGA gain.
4. Gain = 2^{PGAG}
5. After changing the PGA gain setting, a minimum of 2 ADC+PGA conversions should be ignored.
6. Limit the input signal swing so that the PGA does not saturate during operation. Input signal swing is dependent on the PGA reference voltage and gain setting.

6.6.2 CMP and 6-bit DAC electrical specifications

Table 31. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	µA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	µA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns

Table continues on the next page...

Table 31. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}-0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

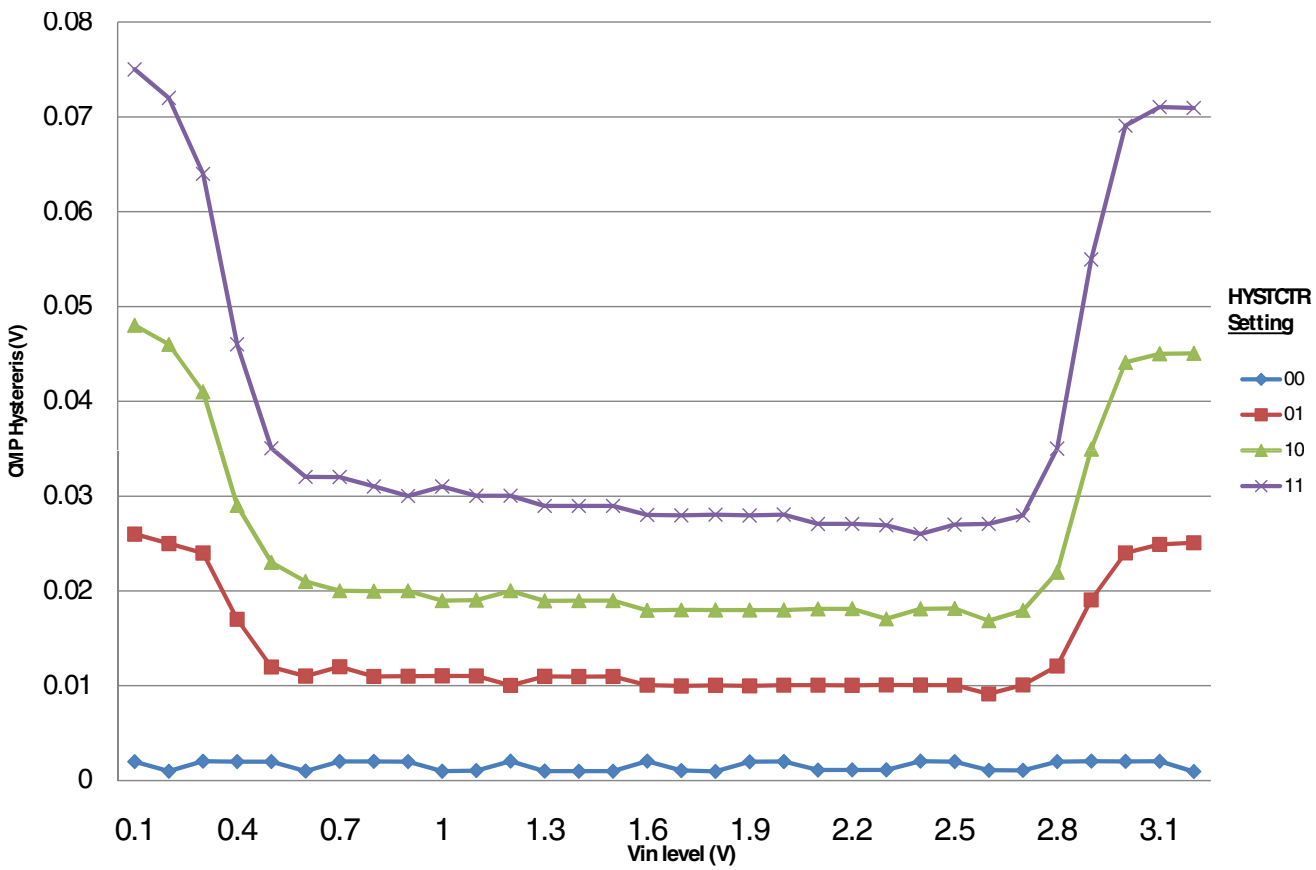


Figure 15. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=0)

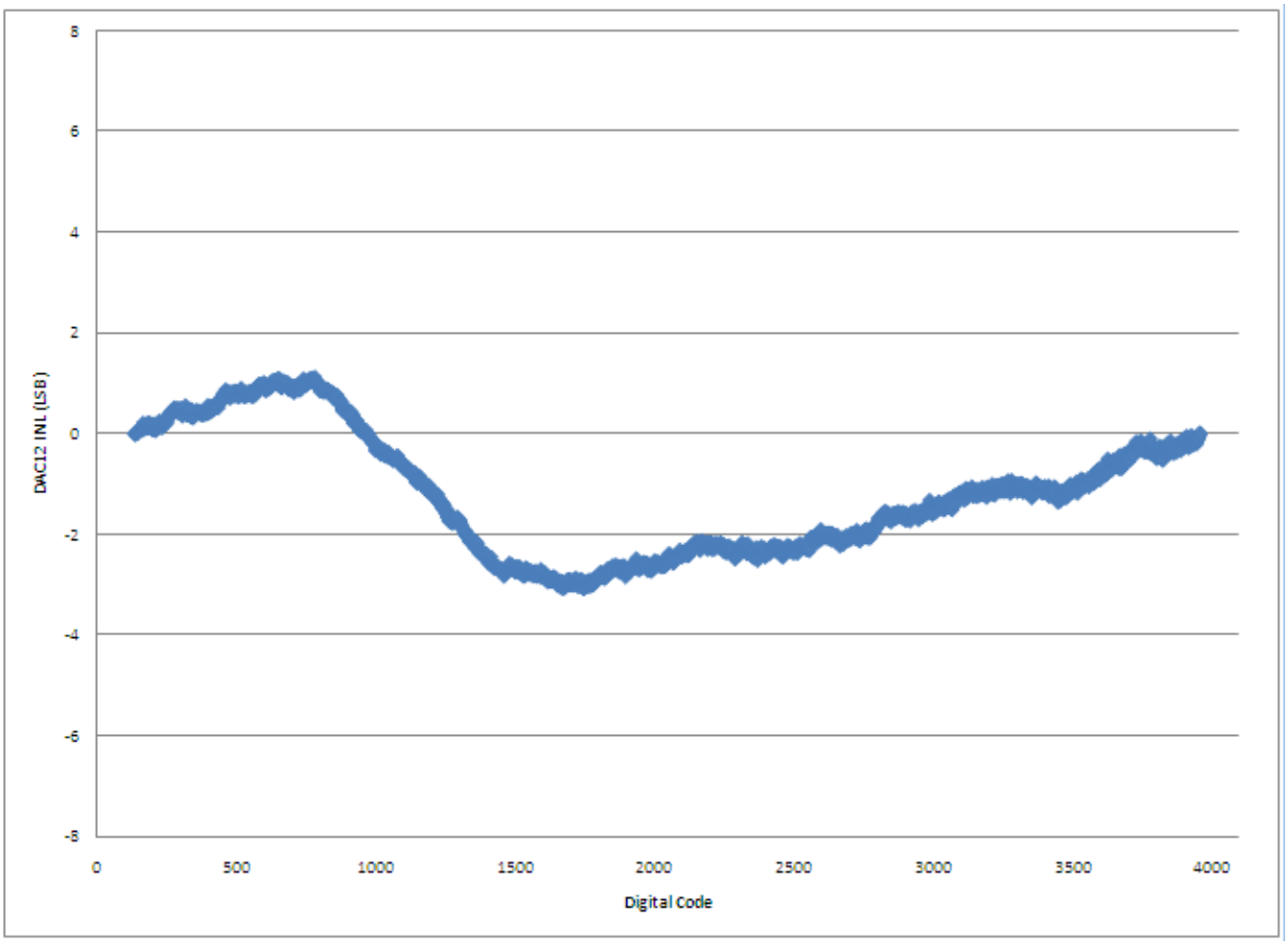


Figure 17. Typical INL error vs. digital code

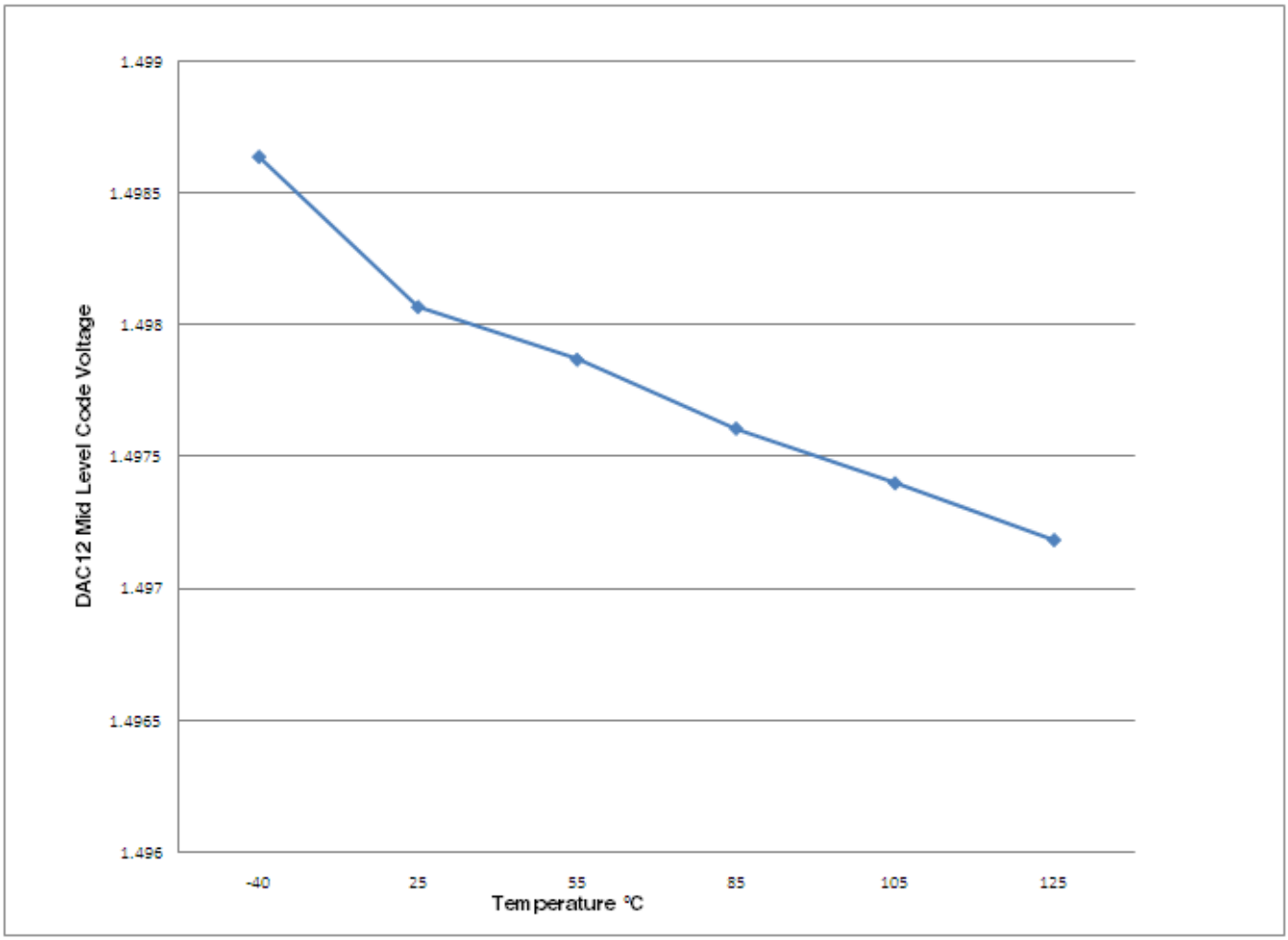


Figure 18. Offset at half scale vs. temperature

6.6.4 Voltage reference electrical specifications

Table 34. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

Table 35. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	
V_{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	
V_{step}	Voltage reference trim step	—	0.5	—	mV	
V_{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range)	—	—	80	mV	
I_{bg}	Bandgap only current	—	—	80	µA	1
I_{lp}	Low-power buffer current	—	—	360	uA	1
I_{hp}	High-power buffer current	—	—	1	mA	1
ΔV_{LOAD}	Load regulation • current = + 1.0 mA • current = - 1.0 mA	 — —	 2 5	 — —	mV	1, 2
T_{stup}	Buffer startup time	—	—	100	µs	
V_{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 36. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	°C	

Table 37. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	

6.7 Timers

See General switching specifications.

6.8 Communication interfaces

Table 40. Master mode DSPI timing (full voltage range) (continued)

Num	Description	Min.	Max.	Unit	Notes
DS2	DSPI_SCK output high/low time	(t_{SCK}/2) - 4	($t_{SCK/2}$) + 4	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	(t_{BUS} x 2) – 4	—	ns	2
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	(t_{BUS} x 2) – 4	—	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	—	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-4.5	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	20.5	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

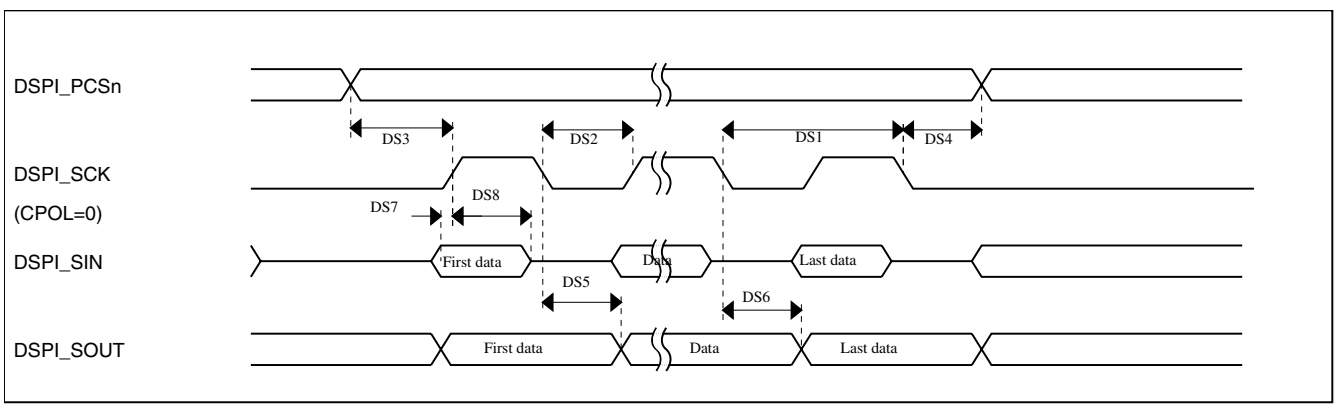


Figure 21. DSPI classic SPI timing — master mode

Table 41. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz
DS9	DSPI_SCK input cycle time	8 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	(t_{SCK}/2) - 4	($t_{SCK/2}$) + 4	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	20	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	19	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	19	ns

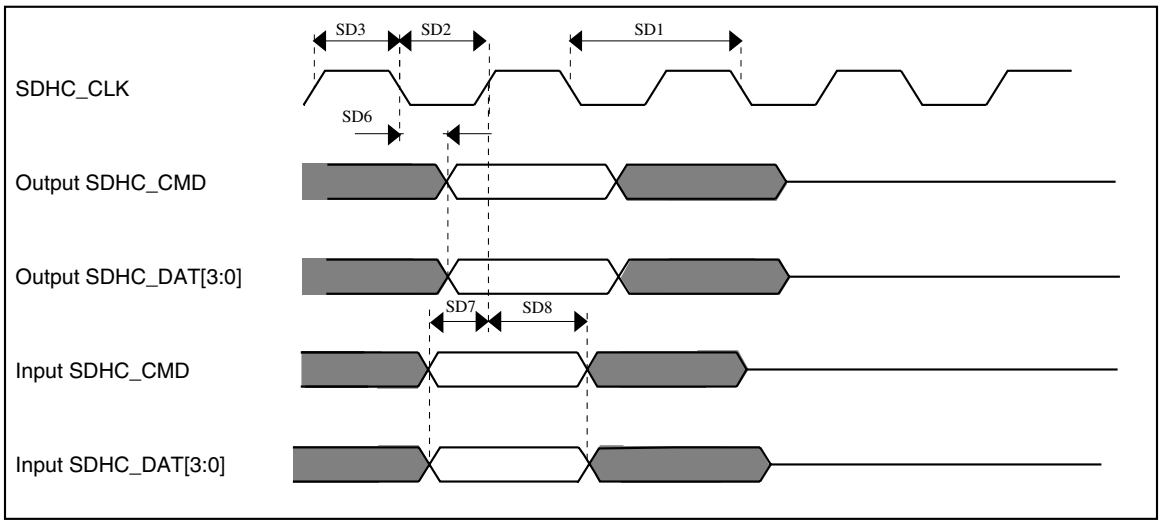


Figure 24. SDHC timing

6.8.7 I²S switching specifications

This section provides the AC timings for the I²S in master (clocks driven) and slave modes (clocks input). All timings are given for non-inverted serial clock polarity (TCR[TSCKP] = 0, RCR[RSCKP] = 0) and a non-inverted frame sync (TCR[TFSI] = 0, RCR[RFSI] = 0). If the polarity of the clock and/or the frame sync have been inverted, all the timings remain valid by inverting the clock signal (I2S_BCLK) and/or the frame sync (I2S_FS) shown in the figures below.

Table 44. I²S master mode timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S1	I2S_MCLK cycle time	2 x t_{SYS}		ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_BCLK cycle time	5 x t_{SYS}	—	ns
S4	I2S_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_BCLK to I2S_FS output valid	—	15	ns
S6	I2S_BCLK to I2S_FS output invalid	-2.5	—	ns
S7	I2S_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_BCLK to I2S_TXD invalid	-3	—	ns
S9	I2S_RXD/I2S_FS input setup before I2S_BCLK	20	—	ns
S10	I2S_RXD/I2S_FS input hold after I2S_BCLK	0	—	ns

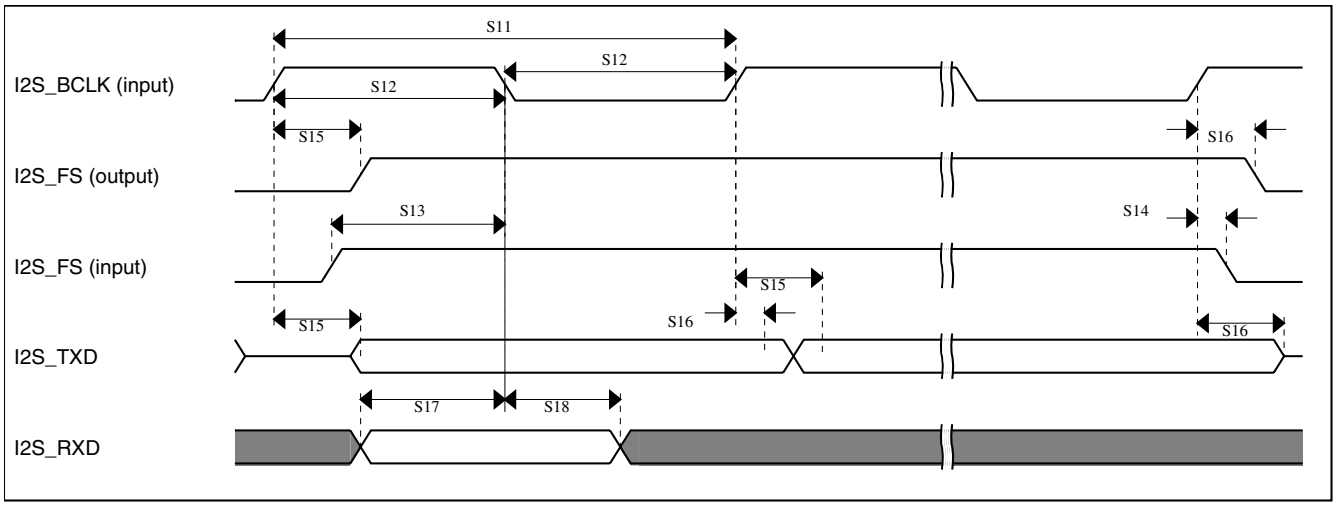


Figure 26. I²S timing — slave modes

Table 46. I²S master mode timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	2 x t_{SYS}		ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_BCLK cycle time	5 x t_{SYS}	—	ns
S4	I2S_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_BCLK to I2S_FS output valid	—	15	ns
S6	I2S_BCLK to I2S_FS output invalid	-4.3	—	ns
S7	I2S_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_BCLK to I2S_TXD invalid	-4.6	—	ns
S9	I2S_RXD/I2S_FS input setup before I2S_BCLK	23.9	—	ns
S10	I2S_RXD/I2S_FS input hold after I2S_BCLK	0	—	ns

Table 47. I²S slave mode timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_BCLK cycle time (input)	8 x t_{SYS}	—	ns
S12	I2S_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_FS input setup before I2S_BCLK	10	—	ns
S14	I2S_FS input hold after I2S_BCLK	3.5	—	ns
S15	I2S_BCLK to I2S_TXD/I2S_FS output valid	—	28.6	ns
S16	I2S_BCLK to I2S_TXD/I2S_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_BCLK	10	—	ns
S18	I2S_RXD hold after I2S_BCLK	2	—	ns

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 48. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DDTSI}	Operating voltage	1.71	—	3.6	V	
C_{ELE}	Target electrode capacitance range	1	20	500	pF	1
f_{REFmax}	Reference oscillator frequency	—	5.5	12.7	MHz	2
f_{ELEmax}	Electrode oscillator frequency	—	0.5	4.0	MHz	3
C_{REF}	Internal reference capacitor	0.5	1	1.2	pF	
V_{DELTA}	Oscillator delta voltage	100	600	760	mV	4
I_{REF}	Reference oscillator current source base current • 1uA setting (REFCHRG=0) • 32uA setting (REFCHRG=31)	— —	1.133 36	1.5 50	µA	3 , 5
I_{ELE}	Electrode oscillator current source base current • 1uA setting (EXTCHRG=0) • 32uA setting (EXTCHRG=31)	— —	1.133 36	1.5 50	µA	3 , 6
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	7
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
MaxSens	Maximum sensitivity	0.003	12.5	—	fF/count	10
Res	Resolution	—	—	16	bits	
T_{Con20}	Response time @ 20 pF	8	15	25	µs	11
I_{TSI_RUN}	Current added in run mode	—	55	—	µA	
I_{TSI_LP}	Low power mode current adder	—	1.3	2.5	µA	12

1. The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.
2. CAPTRM=7, DELVOL=7, and fixed external capacitance of 20 pF.
3. CAPTRM=0, DELVOL=2, and fixed external capacitance of 20 pF.
4. CAPTRM=0, EXTCHRG=9, and fixed external capacitance of 20 pF.
5. The programmable current source value is generated by multiplying the SCANC[REFCHRG] value and the base current.
6. The programmable current source value is generated by multiplying the SCANC[EXTCHRG] value and the base current.
7. Measured with a 5 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 8; Iext = 16.
8. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 2; Iext = 16.
9. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 16, NSCN = 3; Iext = 16.
10. Sensitivity defines the minimum capacitance change when a single count from the TSI module changes, it is equal to (C_{ref} * I_{ext})/(I_{ref} * PS * NSCN). Sensitivity depends on the configuration used. The typical value listed is based on the following configuration: Iext = 5 µA, EXTCHRG = 4, PS = 128, NSCN = 2, $I_{ref} = 16$ µA, REFCHRG = 15, C_{ref} = 1.0 pF. The minimum sensitivity describes the smallest possible capacitance that can be measured by a single count (this is the best sensitivity but is described as a minimum because it's the smallest number). The minimum sensitivity parameter is based on the following configuration: $I_{ext} = 1$ µA, EXTCHRG = 0, PS = 128, NSCN = 32, $I_{ref} = 32$ µA, REFCHRG = 31, C_{ref}= 0.5 pF
11. Time to do one complete measurement of the electrode. Sensitivity resolution of 0.0133 pF, PS = 0, NSCN = 0, 1 electrode, DELVOL = 2, EXTCHRG = 15.
12. CAPTRM=7, DELVOL=2, REFCHRG=0, EXTCHRG=4, PS=7, NSCN=0F, LPSCNITV=F, LPO is selected (1 kHz), and fixed external capacitance of 20 pF. Data is captured with an average of 7 periods window.

144 LQFP	144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
35	K3	ADC1_SE16/ CMP2_IN2/ ADC0_SE22	ADC1_SE16/ CMP2_IN2/ ADC0_SE22	ADC1_SE16/ CMP2_IN2/ ADC0_SE22								
36	J3	ADC0_SE16/ CMP1_IN2/ ADC0_SE21	ADC0_SE16/ CMP1_IN2/ ADC0_SE21	ADC0_SE16/ CMP1_IN2/ ADC0_SE21								
37	M3	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18								
38	L3	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23								
39	L4	DAC1_OUT/ CMP2_IN3/ ADC1_SE23	DAC1_OUT/ CMP2_IN3/ ADC1_SE23	DAC1_OUT/ CMP2_IN3/ ADC1_SE23								
40	M7	XTAL32	XTAL32	XTAL32								
41	M6	EXTAL32	EXTAL32	EXTAL32								
42	L6	VBAT	VBAT	VBAT								
43	—	VDD	VDD	VDD								
44	—	VSS	VSS	VSS								
45	M4	PTE24	ADC0_SE17	ADC0_SE17	PTE24	CAN1_TX	UART4_TX			EWM_OUT_b		
46	K5	PTE25	ADC0_SE18	ADC0_SE18	PTE25	CAN1_RX	UART4_RX			EWM_IN		
47	K4	PTE26	DISABLED		PTE26		UART4_CTS_ b			RTC_CLKOUT		
48	J4	PTE27	DISABLED		PTE27		UART4_RTS_ b					
49	H4	PTE28	DISABLED		PTE28							
50	J5	PTA0	JTAG_TCLK/ SWD_CLK/ EZP_CLK	TSI0_CH1	PTA0	UART0_CTS_ b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
51	J6	PTA1	JTAG_TDI/ EZP_DI	TSI0_CH2	PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
52	K6	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSI0_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
53	K7	PTA3	JTAG_TMS/ SWD_DIO	TSI0_CH4	PTA3	UART0_RTS_ b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
54	L7	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSI0_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
55	M8	PTA5	DISABLED		PTA5		FTM0_CH2		CMP2_OUT	I2S0_RX_ BCLK	JTAG_TRST	
56	E7	VDD	VDD	VDD								
57	G7	VSS	VSS	VSS								
58	J7	PTA6	DISABLED		PTA6		FTM0_CH3				TRACE_ CLKOUT	
59	J8	PTA7	ADC0_SE10	ADC0_SE10	PTA7		FTM0_CH4				TRACE_D3	

144 LQFP	144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
143	C2	PTD14	DISABLED		PTD14	SPI2_SIN		SDHC0_D6		FB_A22		
144	C1	PTD15	DISABLED		PTD15	SPI2_PCS1		SDHC0_D7		FB_A23		

8.2 K10 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.